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PHD-EE-2013

SUBJECT: Electronics & Communication Engineering

		Sr. No
Time: 11/4 Hours	Max. Marks: 100	Total Questions: 10
Candidațe's Name		
Father's Name		
Roll No. (in figures)		
Date of Examination		and the second
(Signature of the Candidate)		(Signature of the Invigilator)

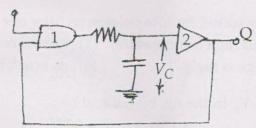
CANDIDATES MUST READ THE FOLLOWING INFORMATION/INSTRUCTIONS BEFORE STARTING THE QUESTION PAPER.

- 1. All questions are compulsory and carry equal marks.
- 2. All the candidates must return the question booklet as well as OMR Answer-Sheet to the Invigilator concerned before leaving the Examination Hall, failing which a case of use of unfair-means/misbehaviour will be registered against him/her, in addition to lodging of an FIR with the police. Further the answer-sheet of such a candidate will not be evaluated.
- 3. In case there is any discrepancy in any question(s) in the Question Booklet, the same may be brought to the notice of the Controller of Examinations in writing within two hours after the test is over. No such complaint(s) will be entertained thereafter.
- 4. The candidate must not do any rough work or writing in the OMR Answer-Sheet. Rough work, if any, may be done in the question booklet itself. Answers Should Not be ticked in the question booklet.
- 5. Use black or blue ball point pen only in the OMR Answer-Sheet.
- 6. For each correct answer, the candidate will get full credit. Cutting, erasing, overwriting and more than one answer in OMR Answer-Sheet will be treated as incorrect answer. There will be No Negative marking.
- 7. Before answering the questions, the candidates should ensure that they have been supplied correct and complete booklet. Complaints, if any, regarding misprinting etc. will not be entertained 30 minutes after starting of the examination.

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- 1. The characteristics equation of T-flip flop is given by:

 - (1) $Q = \overline{T}Q + T\overline{Q}$ (2) $Q = T\overline{Q} + Q\overline{T}$ (3) Q = TQ (4) $Q = T\overline{Q}$
- **2.** The multivibrator shown in the figure has $R = 300 \Omega$ and $C_1 = 500 \text{ pf}$. Then the pulse width is:



- (1) 1 n sec
- (2) 1 µ sec
- (3) 10 n sec
- (4) 1 m sec

- 3. PROMs are used to store:
 - (1) Bulk information

- (2) Sequential information
- (3) Information to be accessed rarely
- (4) Relatively permanent information
- 4. A single instruction to clear the lower four bits of accumulator in 8085 assembly language is:
 - (1) XRI OFH
- (2) ANI FOH
- (3) XRI FOH
- (4) ANI CFH
- 5. 2's complement representation of a 16 bit number (one sign bit and 15 magnitude bits) is FFF1. Its magnitude in decimal representation is:
 - (1) 0
- (2) 1
- (3) 32,767
- (4) 65,767
- 6. If the accumulator of 8085 contains 37 H and the previous operation has set the carry flag, the instruction ACI. 56 H will result in :
 - (1) 8 DH
- (2) 8 EH
- (3) 17 H
- (4) 18 H

- 7. In standard TTL, 'Totem Pole' stage refers to:
 - (1) Multi-emitter input stage
- (2) Phase splitter

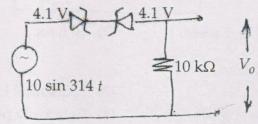
(3) Output buffer

- (4) Open collector output stage
- 8. An 8085 up based system drives a multiplexed 5-digits, 7-segments display. The digits are refreshed at a rate of 500 Hz. The ON time for each digit is:
 - (1) 4 ms
- (2) 0.4 ms
- (3) 10 ms
- (4) 25 ms
- 9. Serial input data of 8085 can be loaded into bit 7 of the accumulator by:
 - (1) Executing RIM instruction
- (2) Execution of RST-1

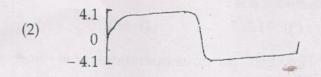
(3) Using TRAP

(4) None of these

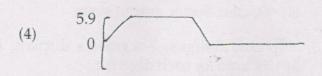
- 10. A memory system of size 16 k bytes is required to be designed using memory chip which have 121 address lines and 4 data lines each. Number of such chips required design the memory system is:
 - (1) 2
- (2) 4
- (3) 8
- (4) 16
- 11. Silicon diode is less suited for low voltage rectifier operation, because :
 - (1) it can withstand high temperature (2) its reverse saturation current is low
 - (3) its cut-in voltage is high
- (4) its break down voltage is high
- The waveshape of V_0 in the fig. below will be:











- 13. The static characteristics of an adequately forward biased p-n junction is a straight line, if the plot is of:
 - (1) $\log I \, v/s \log V$

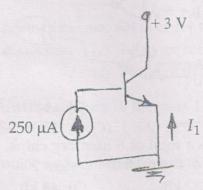
(2) $\log I \, \text{v/s} \, V$

(3) $I \text{ v/s} \log V$

(4) I v/s V

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(1) 0.53 V

D

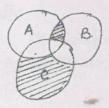
- (2) 0.7 V
- (3) 0.84 V
- (4) 0.98 V

- **15.** In the above problem current I_1 is:
 - (1) 12.75 mA
- (2) 12.75 mA
- (3) 12.5 mA
- $(4) 12.5 \, \text{mA}$
- **16.** The approximate value of input impedance of a common emitter amplifier with emitter resistance R_e given by:
 - (1) $hie + A_I R_e$

(2) $hie + (1 + h_{fe})R_e$

(3) hie

- $(4) (1 + h_{fe})R_e$
- 17. Boolean expression for shaded area is:

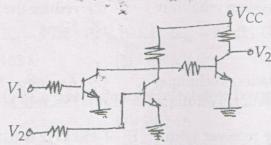


(1) $AB + \overline{BC}$

(2) $ABC + A\overline{B}\overline{C}$

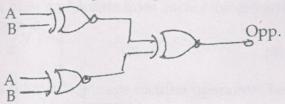
(3) $AB\overline{C} + \overline{AB}C + \overline{AB}$

- (4) $\overline{AB}C + AB$
- 18. The circuit of a gate in the RTL family shown in the figure is a/an:



- (1) AND gate
- (2) OR gate
- (3) NAND gate
- (4) NOR gate

19. The output of the circuit shown in figure is equal to:



(1) 0

(2) 1

(3) $\overline{A}B + A\overline{B}$

 $(4) \quad (\overline{A \times B}) \times (\overline{A \times B})$

20. The memory system has a total of 8 memory chips, each with 12 address lines and data lines. The total size of the memory system is:

(1) 6 kB

(2) 32 kB

(3) 48 kB

(4) 64 kB

21. One of the following consisting of non-resonant antenna:

(1) Rohmbic

(2) Folded dipole

(3) End fire array

- (4) Broad side array
- 22. In feedback amplifier the gain is:

(1) independent of β

(2) directly proportional to β

(3) inversely proportional to β

(4) zero

23. An FM signal, with a deviation *S*, is passed through a miner and has its frequency reduced five fold. The deviation in the output of the mixer is:

(1) 58

(2) 6/5

(3) in terminate

(4) δ

24. Harmonic generators use:

(1) Class A Amplifier

(2) Class AB Amplifier

(3) Class B Amplifier

(4) Class C Amplifier

25. Synchronous satellites orbit the earth once in:

(1) 24 Hours

(2) 12 Hours

(3) 6 Hours

(4) 1 Hour

26. A fading margin is included in radio link design to:

(1) improve the system reliability

(2) reduce the required transmitter power

(3) Both

(4) None

27. PPM is a:

(1) Linear Modulation Technique

(2) Analogue Modulation Technique

(3) Digital Modulation Technique

(4) Discrete Modulation Technique

28. A superhetrodyne receiver with an IF of 450 kHz is tuned to signal of 1200 kHz, the image frequency is :

(1) 750 kHz

(2) 1500 kHz

(3) 2250 kHz

(4) 2100 kHz

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29.				(4)	Nights
30.	A telephone receiver uses a permanent m (1) avoid second harmonic distortion (3) give a large bandwidth	(2)			
31.	"SPUTNIK-1" was launched by the count (1) USA, 1957 (2) USSR, 1957			(4)	USSR, 1959
32.	The power gain of a horn antenna of square 4λ :	ıare	e aperture. Let th	ne di	imension of each side
		(3)	194.35	(4)	190.46
33.	How many stations are spread over India (1) 600 (2) 700 (r Indian Doorda 800		n ? - 1000
34.	Which shift keying technique is used in w (1) PSK (2) BPSK (eless/mobile com MSK		nication ? QPSK
35.	For $\varepsilon_b/N_o = 7 dB$ in case of 16 QAM probability:				
	(1) 4.4×10^{-2} (2) 2.4×10^{-4} ((3)	4.4×10^{-4}	(4)	2.4×10^{-2}
36.	Which <i>one</i> is the error correction code?				
			Golay code		
	(3) Convolution code	(4)	Binary code		
37.	VSAT stands for :		1 %		
			Very Small Aper		
	(3) Very Small Area Tropical	4)	Very Small Aper	ture	e Tropical
38.	The noise temperature of a 6 GHz recienoise temperatures:	ver	system having	the	following gains and
	$T_{in} = 75k \ T_{rf} = 75k \ , \ T_m = 400k \ , \ T_{if_p} = 100k \ , \ T_{if_p} = 10$	100	$0k, G_{xf} = 23 \mathrm{dB},$	G_m	$= 0 \mathrm{dB}, \; G_{if} = 35 \mathrm{dB}.$
	(1) $150 K$ (2) $153 K$ (3)	3)	155 K	(4)	157 K
39.	Which one is analog multiple access techn	niqu	ie in satellite con	ımu	nication ?
	(4) 7777 4		FDMA		peri sapro a .+g
	(3) CDMA	4)	Multi Carrier CI)MA	

40.). Input impedance of an circuited loss line of	of length λ is:
	(2) 6: 1	2) finite capacitive reactance
	(3) finite inductive reactance (4)	4) None of the above
41.	. The units of pulse dispersion in optical fib	ere is:
	(1) ns/km.nm (2) ns/km. (3)	3) ns (4) None of the a
42.	2. 1 μW power corresponds to :	
	(1) 10 10	(4) - 30 dB
43.	The process of combining text with symbo	
	(1) Mark up (2) Combination (3)	
44.	. What does PBX stands for ?	(1) Mining
	(1) Print P 1 T 1) Public Branch Exchange
	(2) D:	Private Box Exchange
45		
0.	. Computers printers or cash registers are extended (1) DCE (2) Mux (3)	
40	(),) DTE (4) Code sets
40.	Which organization is responsible for creat	
) IBM (4) IEEE
47.	The range over which an optical source em	its light is known as :
	(1) Line width (2) Beam width (3)	Band width (4) HPBW
48.	For the system $X = \begin{bmatrix} 2 & 0 \\ 0 & 4 \end{bmatrix} X + \begin{bmatrix} 2 \\ 1 \end{bmatrix} u$; $y \begin{bmatrix} 40 \end{bmatrix}$	X with u as unit impulse and with
	initial state, the output, y, becomes:	
	(1) $2e^{2t}$ (2) $4e^{2t}$ (3)	$2e^{4t}$ (4) $4e^{4t}$
49.	50 dB, 1024 quantizing levels, then <i>L</i> is:	inimum signal to noise ratio requi
	(1) 1002 (2) 1008 (3)	1006 (4) 1012
50.	(3)	pulse repetition frequency transmitted power
		,

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51.	A Silica fibre has measured losses of 1.5 dB/kr a total fibre loss of 20 dB can be tolerated in a		
	repeater spacing for operation at 1.3 μ m: (1) 8.4 km (2) 13.3 km (3) 15		
52.	How many times is the value of $\frac{a}{\lambda}$ is approx	ximately larger	for parabolic refractive
	index profile single mode fibre than for a single (1) 1.4 (2) 2.4 (3) 2.5		
53.	Left the value of critical angle is 73.2° and ref Determine the refractive index of the another n		of first medium is 1.52.
	(1) 2.12 (2) 1.98 (3) 1.5	.56	4) 1.46
54.	Which one is TEM mode of propagation of ligh	ht?	ibandingana (1)
	(1) $E = E_t$, $E_z = 0$, $E_z \neq 0$ (2) H (3) $E = F_z$, $H = H_t$, $E_z = 0$, $H_z = 0$ (4) E		
55.	i. What is the ratio of stimulated emission rate incandescent lamp operating at wavelength of (1) 3.21×10 ⁻³ (2) 3.21×10 ⁻⁵ (3) 2.	1.5 µm and at a	temperature of 900 K:
56.	Photons of energy 4.5×10 ⁻²¹ J are incided responsivity 0.9 A/W. If the optical power level current generated:		
	(1) $10 \mu\text{A}$ (2) 10mA (3) 15μ	5 μΑ ((4) 18 μΑ
57.	Which of the following photodetectors has the link?	he fastest respo	onse time for fibre optic
	(1) Photo transistor (2) Li	ight dependent	resistor
	(3) PIN diode (4) Ph	hotodiode	
58.	The configuration utilized by a line commun data at a rate of 100 mbps is:	nication system	capable of transmitting
	그 그 그 그 그 그 그 그 그 그 그 그 그 그 그 그 그 그 그	pen wire line sy	
	(3) optical fibre system (4) tw	wisted wire syst	rem
59.	(1) changing the doping level of semiconductor	ors	
	(2) using different band gap semiconductors (3) increasing the applied voltage		Britania - ng
	(3) increasing the applied voltage		

D

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	60. Assuming a correspondir (1) 25 MHz		7.	
,		(-) / U. / IVI	(-) 100 1411	Hz (4) 50 MHz
	(2) reduction	in path loss by 6 c in path loss by 12	1D	oe:
6	2. Ultra Wide Ba	nd technology is u	used primarily for:	
	(2) displaying (3) transmittir	web pages on a ce	inside a home at ver	
63	B. For a cluster of	Size 7 the carrier	t in the striate city	
	(1) 73.5	(2) 147	to- interference ratio	C/I is approximately :
64		(-) -1	(3) 1.5	(1) 7
65.	(3) intermodula	nterference ation	(2) adjacent (4) received (channel interference desensitization despectrum US-AMPS cell
	(1) 312	(2) 416	(3) 666	(4) 822
66.	The distributed of (1) Frequency set (3) Signal to noise	lynamic channel a ense distance se ratio	ssignments scheme i	s primarily based on .
67.			(4) Either (1) o	or (2) or (3)
	(1) $\lambda e^{-2\lambda T}$	pure ALOHA syst (2) $\lambda e^{-\lambda T}$	em is given by:	
68.	The channel 1		$(3) (1/\lambda) e^{-2\lambda T}$	(4) $(1/\lambda) e^{2\lambda T}$
		(4) 23 KHZ	S-54 cellular standard (3) 30 kHz	(4) 200 LTT
69.	The ε_b/N_o is usupropagation condition	ally of what value	which depends on y scheme used in CD	
	(1) 6 dB	(2) 9 dB		MA systems:
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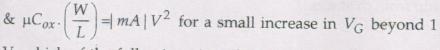
8	31. The open loop DC gain of a unifunction $\frac{s+4}{s^2+75+13}$ is:	ty negative feedback	system with closed loo	p trans
	$(1) \frac{4}{13} \qquad (2) \frac{4}{9}$	(3) 4	(4) 13	
8	2. The transfer 6			
	2. The transfer function of a tachon	neter is of the form:		
	(1) ks (2) $\frac{k}{s}$	$(3) \frac{k}{s+1}$	$(4) \frac{k}{s(s+1)}$	
83	A system represented by $\frac{dy}{dt}$ + response will be:	$-2y = 4t \ u(t). $ The ra	imp component in the	e force
	response will be:		. I the tit	c lorce
	(1) t u(t) (2) 2t u(t)	(3) 3t u(t)	(4) 11t 11(t)	
84	If the feedback control system is cis:	of type 2, then the ste	ady state error for a ran	np inpu
	(1) Infinite (2) Constant	(3) Zero	(4) Indeterminat	
85.	The closed loop transfer function (of a control system is	given by $\frac{C(s)}{D(s)} = \frac{2(s)}{(s-s)^2}$	(S-1)
	r - Fat the output is		R(S) (S+2)	(S+1)
	(1) $-3e^{-2t} + 4e^{-t} - 1$ (3) Zero	(2) $-3e^{-2t} - 4$ (4) Infinity	$4e^{-t} + 1$	
86.	For characteristic equation of a -l			
	For characteristic equation of a closed-loop behaviour can be $(1) \ 0 < k < 10$ $(2) \ k > 10$	osed loop system S' e ensured when gain (3) $-\infty \le k > \infty$	$^{+} + 6S^{3} + 11S^{2} + 6S + $ k is such that	-k=0
87.	The phase margin of a		(1) 0 \ R \ \ 20	
	The phase margin of a syst $G(s) H(s) = \frac{(1-s)}{(1+s)(2+s)}$ is:	em with the ope	en loop transfer fu	nction
	(1) 0 (2) 63.4°	(3) 90°	(4) ∞	
88.	The system shown in fig. remains sta	able when :		
		k s ⁻¹	1	

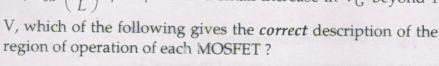
Y(s)

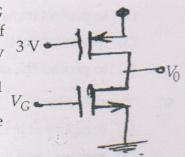
(1) k < -1 (2) -1 < k < 1 (3) 1 < k < 3 (4) k > 3 PHD-EE-2013/Elec. & Com. Engg./(D)

- In the Bode plot of a unity feedback control system, the value of phase of G (jw) at the gain cross over frequency is -125°. The phase margin of the system is:
 - $(1) 125^{\circ}$
- (3) 55°
- In a synchronous error detector, the output voltage is proportional to $[w(t)]^n$, where w(t) is the rotor velocity and n equals:
 - (1) -2
- (2) 1

- (4) 2
- 91. Consider the CMOS circuit shown where the gate voltage V_G of the n-MOSFET is increased from 0 to high, while the V_G of p-MOSFET is kept constant at 3V. Assume Vth for both is 1V







- (1) Both the MOSFETS are in saturation region
- (2) Both the MOSFETS are in triode region
- (3) n-MOSFET in triode region & p-MOSFET in saturation region
- (4) n-MOSFET in saturation & p-MOSFET in triode region
- Estimate the output voltage V_0 for $V_G = 1.5 \,\mathrm{V}$ in above case :

$$(1) \left(4 - \frac{1}{\sqrt{2}}\right)$$

$$(2) \quad \left(4 + \frac{1}{\sqrt{2}}\right) V$$

$$(3) \quad \frac{\sqrt{3}}{2} V$$

(1)
$$\left(4 - \frac{1}{\sqrt{2}}\right)V$$
 (2) $\left(4 + \frac{1}{\sqrt{2}}\right)V$ (3) $\frac{\sqrt{3}}{2}V$ (4) $\left(4 + \frac{\sqrt{3}}{2}\right)V$

- The p-type substrate in a conventional p-n junction isolated integrated circuit should be connected to:
 - (1) no where i.e. left floating
 - (2) a dc ground potential
 - (3) most positive potential available in the circuit
 - most negative potential available in the circuit
- The applical number of diffusions used in making epitaxial-diffused silicon integrated circuit is:
- (2) 2
- (3) 3
- (4) 4

9	5. Epitaxial growth in IC chip:
	(1) may be n-type only
	(2) may be p-type only
	(3) involves growth from liquid phase
	(4) involves growth from gas phase
9	The main purpose of metalization process is:
	(1) to act as heat sink
	(2) to protect transistor from possible thermal runaway
	(5) to interconnect various circuit elements
	(4) to protect the chip from oxidation
97	The till till t
	 component are made by screen and fire process resistor have greater protection, precision and more stable resistor are cheaper than the simple resistors all of these
98.	Channel resistance R_{on} is scaled by a factor:
	(1) $\frac{1}{\alpha}$ (2) $\frac{\beta}{\alpha}$ (3) 1 (4) $\frac{\alpha^2}{\beta}$
99.	Propagation delay and fan out for a standard IC(TTL NAND gate) are:
	(2) pn sec & 15
100.	An ideal n-MOSEET has falled
	An ideal n-MOSFET has following parameters $W = 30 \mu m \mu_n = 450 cm^2 / v - s$, $L = 2\mu_m t_{ox} = 350^\circ A V_{TN} = 0.8v$. If transistor is operating in saturation at $V_{GS} = 4v$ then
	(1) 486 µs (2) 0.213 ms (3) 2.13 ms (4) 48.6 ms